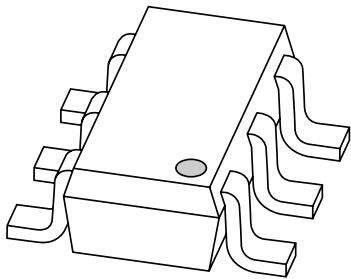


DATA SHEET



PMEG6010AED

Low V_F (MEGA) Schottky barrier diode

Low V_F (MEGA) Schottky barrier diode

PMEG6010AED

FEATURES

- Low switching losses
- Very high surge current absorption capability
- Fast recovery time
- Guard ring protected
- Plastic SMD package.

APPLICATIONS

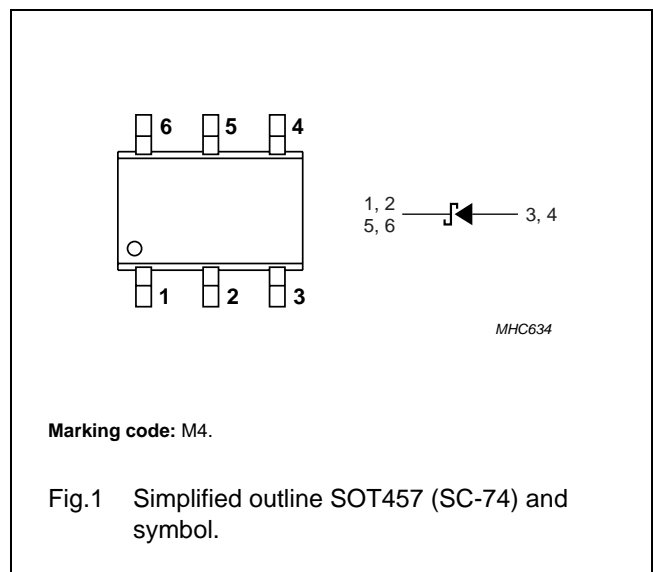
- Low power switched-mode power supplies
- Rectification
- Polarity protection.

GENERAL DESCRIPTION

Planar Schottky barrier diode encapsulated in a SOT457 (SC-74) small plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode



LIMITING VALUES

In accordance with Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	60	V
I_F	continuous forward current	$T_{amb} \leq 25\text{ °C}$; note 1	–	1	A
I_{FSM}	non-repetitive peak forward current	$t = 8\text{ ms}$; square wave	–	17.5	A
I_{RSM}	non-repetitive peak reverse current	$t_p = 100\text{ }\mu\text{s}$	–	0.5	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	+150	°C

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for cathode 6 cm².

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ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ °C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	continuous forward voltage	$I_F = 0.1\text{ A}$	400	mV
		$I_F = 1\text{ A}$	650	mV
I_R	continuous reverse current	$V_R = 60\text{ V}$; see Fig.3	350	μA
		$V_R = 60\text{ V}$; $T_j = 100\text{ °C}$; notes 1 and 2	8	mA
C_d	diode capacitance	$V_R = 4\text{ V}$; $f = 1\text{ MHz}$; see Fig.4	60	pF

Notes

1. Pulse test: $t_p = 300\text{ }\mu\text{s}$; $\delta = 0.02$.
2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications, the reverse power losses P_R are a significant part of the total power losses.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	230	K/W
		in free air; note 2	180	K/W

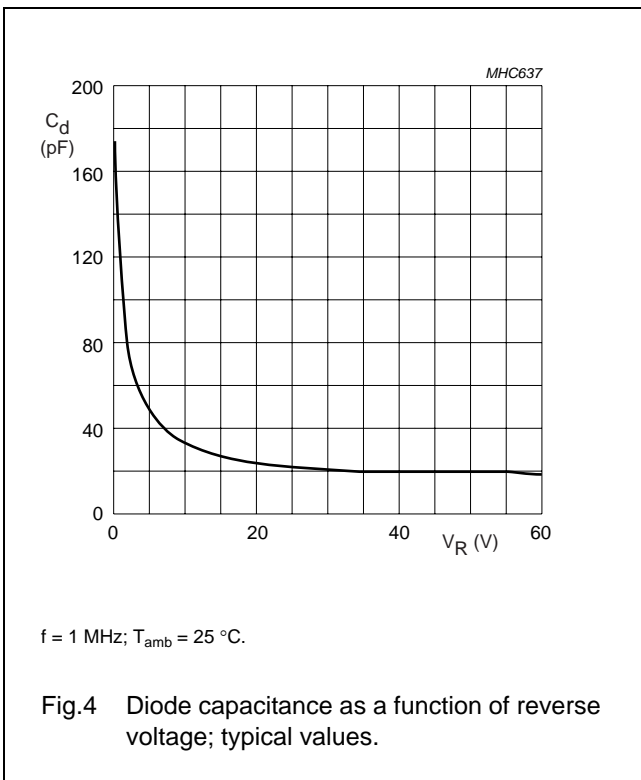
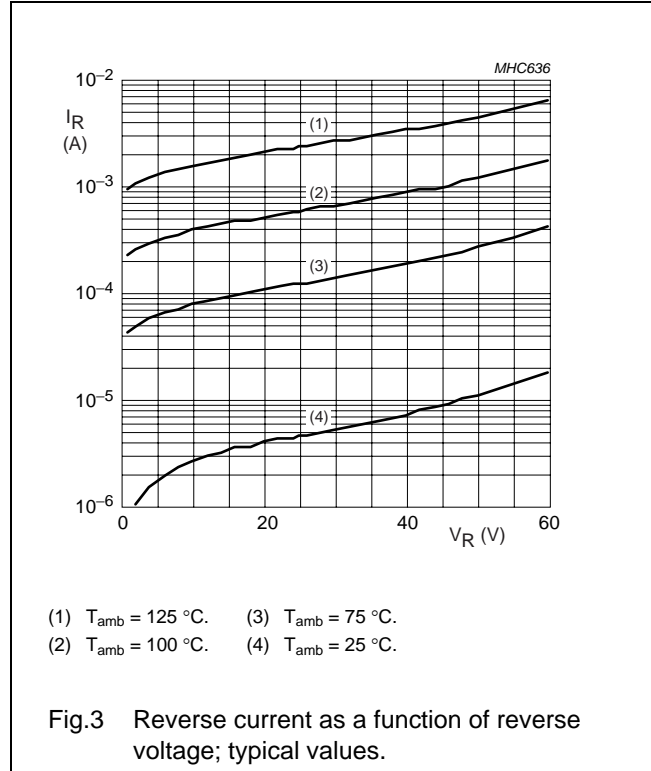
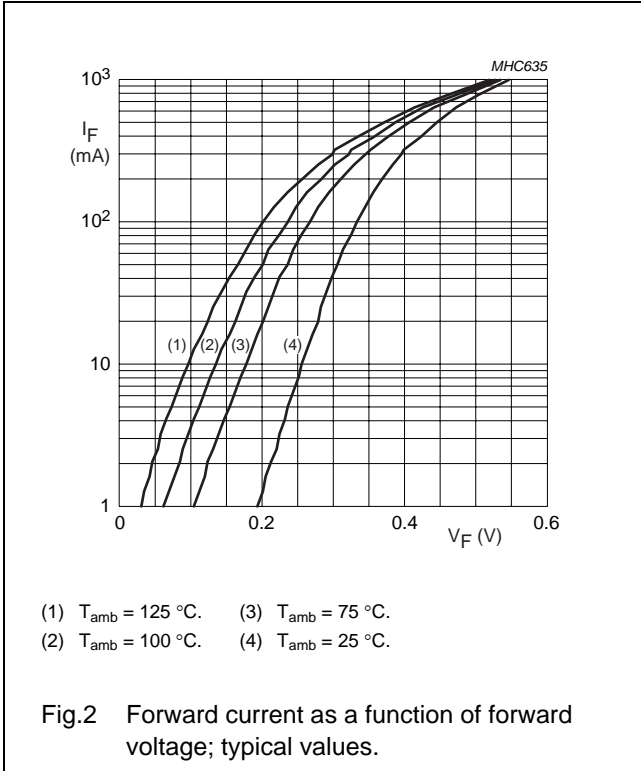
Notes

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm^2 .
2. Device mounted on a printed-circuit board, single-sided copper; tinplated, mounting pad for cathode 6 cm^2 .

Low V_F (MEGA) Schottky barrier diode

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GRAPHICAL DATA



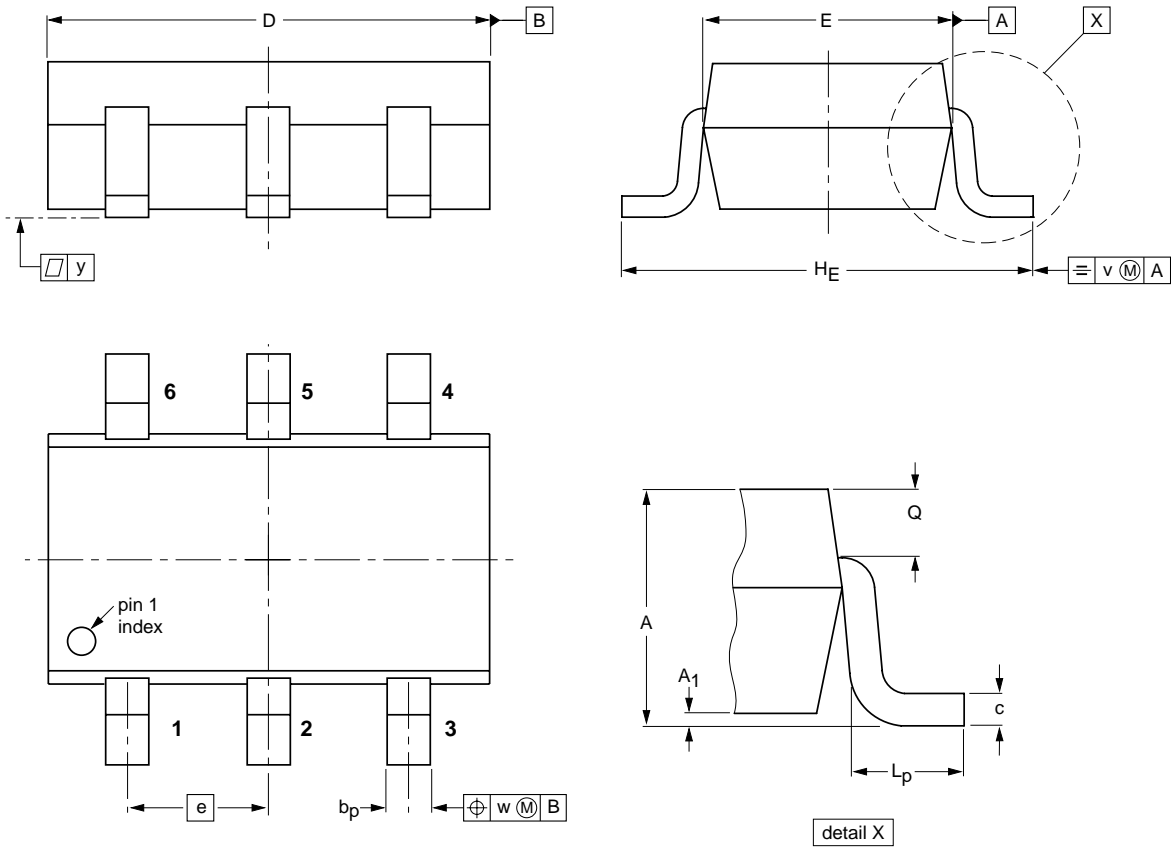
Low V_F (MEGA) Schottky barrier diode

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	c	D	E	e	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT457			SC-74			97-02-28 01-05-04

Low V_F (MEGA) Schottky barrier diode

PMEG6010AED

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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